

STRUCTURE Silicon Monolithic Integrated Circuit

NAME OF PRODUCT DC-AC Inverter Control IC

TYPE BD9766FV

FUNCTION • 2ch control with Half-bridge

· Lamp current and voltage sense feed back control

• Sequencing easily achieved with Soft Start Control

• Short circuit protection with Timer Latch

• Under Voltage Lock Out

• Short circuit protection with over voltage

• Mode-selectable the operating or stand-by mode by stand-by pin

Control PWM and BURST mode by DUTY pin

• BURST mode with 2ch Reverse phase

OAbsolute Maximum Ratings ($Ta = 25^{\circ}C$)

Parameter	Symbol	Limits	Unit
Supply Voltage	Vcc	12	V
Operating Temperature Range	Topr	−35 ~ +85	°C
Storage Temperature Range	Tstg	−55 ~ +125	°C
Power Dissipation	Pd	850*	mW
Maximum Junction Temperature	Tjmax	+125	°C

^{*}Pd derated at 8.5mW/°C for temperature above Ta = 25°C (When mounted on a PCB 70.0mm × 70.0mm × 1.6mm)

ORecommended operating condition

Parameter	Symbol	Range	Unit
Supply voltage	Vcc	5. 0 ~ 11. 0	٧
CT oscillation frequency	fcT	35~200	kHz
BCT oscillation frequency	fBCT	0. 10~0. 50	kHz

Status of this document

The Japanese version of this document is the official specification.

Please use the translation version of this document as a reference to expedite understanding of the official version.

If these is any uncertainty in translation version of this document, official version takes priority.



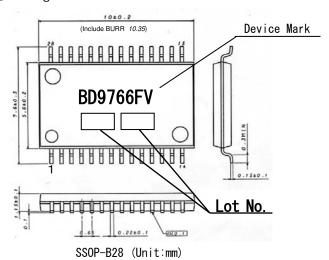
OElectric Characteristics (Ta=25°C, VCC=7V)

Committee Parameter Symbol MIN. TYP MAX. Unit Conditions	<u>DElectric Characteristics</u>	(Ta=25°C, V	VCC=/V)				
COMPALE DEVICE) Departing current Loc1	Parameter	Symbol				llni+	Conditions
Departing current Icol	r di dilio coi	O y III DO 1	MIN.	TYP.	MAX.	OIII C	
Stand-by current Ico2 -	((WHOLE DEVICE))						
COVER VOLTAGE DETECT) FB over voltage detect voltage Vovf 2.70 3.00 3.30 V	Operating current	Icc1	-	9. 0	17. 0	mA	CT=0. 5V
FB over voltage detect voltage	Stand-by current	Icc2	_	4	8	uA	
COUTPUT BLOOK) Peh output voitage H	((OVER VOLTAGE DETECT))			1		1	1
C(OUPPUT BLOOK) Peth output voltage H	FB over voltage detect voltage	Vovf	2. 70	3.00	3, 30	٧	
Peh output voltage H		.1	1		ı	1	
Neh output voltage H		VoutPH	VCC-0, 3	VCC-0, 1	_	٧	
Peh output voltage L VoutPL 0.1 0.3 V					_	٧	
Not not put voltage L VoutNL		VoutPL	_	0. 1	0. 3	٧	
Peh output sink resistance		VoutNL	_	0. 1	0. 3	٧	
Peh output source resistance ReourceP - 10 20 Ω			_			Ω	
Neh output sink resistance							
Not output source resistance RsourceN - 10 20 Ω	·		_	1		1	
(STAND-BY CONTROL)) Stand-by voltage H	*		_				
Stand-by voltage H		1	1	1 10			1
Stand-by voltage L VstL 0.8 V System OFF		VstH	2. 0	_	_	٧	System ON
Hystersis width					0.8		
(TIMER LATCH)) Timer Latch voltage			0, 05	0, 15			,
Timer Latch voltage			0.00		0.20		
Timer Latch current		Vcp	1.5	1 9	2.3	V	
Active edge current Lact L2/RT L5/RT L8/RT A Negative edge current Lneg L2/RDIS L5/RDIS L8/RDIS A Negative edge current Lneg L2/RDIS L5/RDIS L8/RDIS A OSC Max voltage Vosch L8 2.0 2.2 V fact=10kHz OSC Min voltage Vosch L8 2.0 2.2 V fact=10kHz OSC Min voltage Vosch L8 2.0 3.0 UA LIS COMP detect Voltage VISC L9 L9 L9 SS COMP detect Voltage VISC L9 L9 L9 SS COMP detect voltage Vss L9 L9 L9 C(UVLO BLOCK) VISC L9 L9 L9 C(UVLO BLOCK) VISC L9 L9 L9 C(EED BACK BLOCK) VIVIOL L9 L9 L9 L9 L9 L9 L9	-						
Active edge current		1	1			1	
Negative edge current Ineg 1.2/RDIS 1.5/RDIS 1.8/RDIS A	_ ,,	lact	1 2/RT	1 5/RT	1 8/RT	Α	
OSC Max voltage							
Soc Min voltage Voscl 0.3 0.5 0.7 V fneg=100kHz	_ · ·		-			+	fact=10kHz
Soft start current Iss 1.0 2.0 3.0 uA							
IS COMP detect Voltage		1					Theg=100km2
SS COMP detect voltage			1. 0		3. 0	1	
SRT ON resistance RSRT - 200 400 Ω			_		_		
((UVLO BLOCK)) Operating voltage VuvloH 4.25 4.50 4.75 V Shut down voltage VuvloL 4.0 4.25 4.50 V ((FEED BACK BLOCK)) Us IS threshold voltage Vis 1.220 1.250 1.280 V VS threshold voltage Vvs 1.220 1.250 1.280 V IS source current I is1 — — 1.5 uA DUTY=2.0V IS source current I is2 13.0 20.0 27.0 uA DUTY=0V, IS=0.5V VS source current I vs — — 0.9 uA ((BURST MODE)) BOSC Max voltage VburH 1.8 2.0 2.2 V fBct=0.3kHz BOSC Min Voltage VburL 0.3 0.5 0.7 V fBct=0.3kHz BOSC constant current I burosc 1.2/BRT 1.5/BRT 1.8/BRT A <td< td=""><td>_</td><td></td><td>_</td><td></td><td>_</td><td>•</td><td></td></td<>	_		_		_	•	
Operating voltage		RSRT	_	200	400	Ω	
Shut down voltage							
((FEED BACK BLOCK)) IS threshold voltage							
IS threshold voltage		VuvloL	4. 0	4. 25	4. 50	V	
VS threshold voltage	((FEED BACK BLOCK))			T	T	1	
Source current 1	IS threshold voltage	Vis	1. 220	1. 250	1. 280	V	
Is source current 2	VS threshold voltage	Vvs	1. 220	1. 250	1. 280	٧	
VS source current	IS source current 1	lis1	_	_	1.5	uA	DUTY=2. 0V
((BURST MODE)) BOSC Max voltage VburH 1.8 2.0 2.2 V f8cT=0.3kHz BOSC Min Voltage VburL 0.3 0.5 0.7 V f8cT=0.3kHz BOSC constant current Iburosc 1.2/BRT 1.5/BRT 1.8/BRT A ((REG BLOCK)) REG output voltage VREG 3.038 3.100 3.162 V REG source current IREG 5.0 - - mA ((COMP BLOCK)) Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V	IS source current 2	lis2	13. 0	20. 0	27. 0	uA	DUTY=OV、IS=0.5V
BOSC Max voltage	VS source current	lvs	_	_	0. 9	uA	
BOSC Min Voltage	((BURST MODE))						
BOSC constant current Iburosc 1.2/BRT 1.5/BRT 1.8/BRT A ((REG BLOCK))	BOSC Max voltage	VburH	1.8	2. 0	2. 2	٧	fBCT=0. 3kHz
((REG BLOCK)) REG output voltage VREG 3.038 3.100 3.162 V REG source current IREG 5.0 — — mA ((COMP BLOCK)) Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V	BOSC Min Voltage	VburL		0. 5	0. 7	٧	fвст=0. 3kHz
REG output voltage VREG 3.038 3.100 3.162 V REG source current IREG 5.0 — — mA ((COMP BLOCK)) Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V	BOSC constant current	Iburosc	1. 2/BRT	1. 5/BRT	1.8/BRT	A	
REG source current IREG 5.0 — — mA ((COMP BLOCK)) Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V	((REG BLOCK))						
((COMP BLOCK)) Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V		1		3. 100	3. 162	٧	
Over voltage detect VCOMPH 2.20 2.5 2.80 V Under voltage detect VCOMPL 0.590 0.640 0.690 V		IREG	5. 0	_	_	mA	
Under voltage detect VCOMPL 0.590 0.640 0.690 V							
				1			
((PROTECT CLOCK))		VCOMPL	0. 590	0. 640	0. 690	٧	
Normal output voltage VPH 2.9 3.1 3.3 V		VPH	2. 9	3. 1	3. 3	٧	
Protect output voltage VPL 0.5 V	Protect output voltage	VPL	_	_	0. 5	٧	

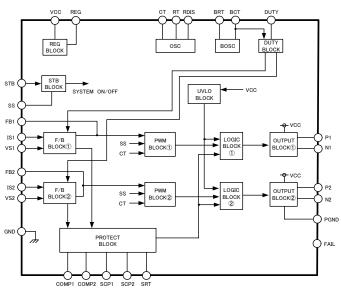
 $(This\ product\ is\ not\ designed\ for\ normal\ operation\ with\ in\ a\ radio\ active\ environment.)$



OPackage Dimensions



OBlock Diagram



OPin Description

Pin No.	Pin Name	Function		
1	DUTY	Control PWM mode and BURST mode		
2	BRT	External resistor from BRT to GND for adjusting the BURST triangle oscillator		
3	BCT	External capacitor from BCT to GND for adjusting the BURST triangle oscillator		
4	RDIS	External resistor from RDIS to GND for adjusting the triangle oscillator		
5	RT	External resistor from SRT to RT for adjusting the triangle oscillator		
6	SRT	External resistor from SRT to RT for adjusting the triangle oscillator		
7	CT	External capacitor from CT to GND for adjusting the triangle oscillator		
8	GND	GROUND		
9	FB1	Error amplifier output①		
10	IS1	Error amplifier input(1)		
11	VS1	Error amplifier input②		
12	FB2	Error amplifier output②		
13	182	Error amplifier input3		
14	VS2	Error amplifier input4		
15	FAIL	Protect clock output		
16	STB	Stand-by switch		
17	COMP1	Under, over voltage detect for 1ch		
18	COMP2	Under, over voltage detect for 1ch		
19	REG	Internal regulator output		
20	SS	External capacitor from SS to GND for Soft Start Control		
21	SCP1	External capacitor from SCP1 to GND for Timer Latch for 1ch		
22	SCP2	External capacitor from SCP2 to GND for Timer Latch for 2ch		
23	P2	FET driver for 2ch		
24	N2	FET driver for 2ch		
25	PGND	Ground for FET drivers		
26	N1	FET driver for 1ch		
27	P1	FET driver for 1ch		
28	Vcc	Supply voltage input		



ONOTE FOR USE

- 1. When designing the external circuit, including adequate margins for variation between external devices and the IC. Use adequate margins for steady state and transient characteristics.
- 2. Recommended Operating Range

The circuit functionality is guaranteed within of ambient temperature operation range as long as it is within recommended operating range. The standard electrical characteristic values cannot be guaranteed at other voltages in the operating ranges, however, the variation will be small.

- 3. Mounting Failures
 - Mounting failures, such as misdirection or miscounts, may harm the device.
- 4. Electromagnetic Fields
 - A strong electromagnetic field may cause the IC to malfunction.
- 5. The GND pin should be the location within $\pm 0.3V$ compared with the PGND pin
- 6. BD9766FV has the short circuit protection with Thermal Shut Down System. When STB or Vcc pin re-supplied, They enables to cancel the latch. If It rise the temperature of the chip more than 170°C (TYP), It make the external FET OFF
- 7. Absolute maximum ratings are those values that, if exceeded, may cause the life of a device to become significantly shortened.
 Moreover, the exact failure mode caused by short or open is not defined. Physical countermeasures, such as a fuse, need to be considered when using a device beyond its maximum ratings.
- 8. About the external FET, the parasitic Capacitor may cause the gate voltage to change, when the drain voltage is switching.

 Make sure to leave adequate margin for this IC variation.
- 9. On operating Slow Start Control (SS is less than 2.2V), It does not operate Timer Latch.
- 1 O. By STB voltage, BD9886FV is changed to 2 states. Therefore, do not input STB pin voltage between one state and the other state $(0.8 \sim 2.0 \text{V})$.
- 1 1. The pin connected a connector need to connect to the resistor for electrical surge destruction.
- 1 2. This IC is a monolithic IC which (as shown is Fig-1)has P* substrate and between the various pins. A P-N junction is formed from this P layer of each pin. For example, the relation between each potential is as follows,
 - O (When GND > PinB and GND > PinA, the P-N junction operates as a parasitic diode.)
 - O(When PinB > GND > PinA, the P-N junction operates as a parasitic transistor.)

Parasitic diodes can occur inevitably in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits as well as operation faults and physical damage. Accordingly you must not use methods by which parasitic diodes operate, such as applying a voltage that is lower than the GND (P substrate) voltage to an input pin.

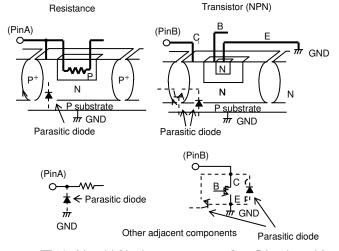


図-1 Simplified structure of a Bipolar IC

Notes

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